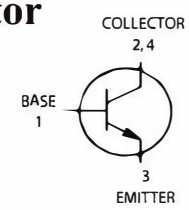
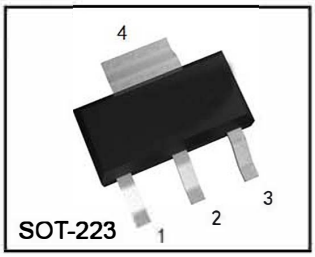
NPN Silicon Planar Epitaxial Transistor





●ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	300	V
Collector-Base Voltage	V_{CBO}	300	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current (DC)	$I_{C(DC)}$	500	mA
Total Device Disspation T_A=25°C	P_D	2	W
Junction Temperature	Tj	150	°C
Storage, Temperature	Tstg	-55 to +150	°C

● Device Marking

ZTA42

● ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage (I_C=1mA)	$V_{(BR)CEO}$	300	-	-	V
Collector-Base Breakdown Voltage (I_C=100μA)	$V_{(BR)CBO}$	300	-	-	V
Emitter-Base Breakdown Voltage (I_E=10 μA)	$V_{(BR)EBO}$	6	-	-	V
Collector-Emitter Cutoff Current (V_{CB}=300V)	I_{CBO}	-	-	100	nA
Emitter-Base Cutoff Current (V_{EB}=6V)	I_{EBO}	-	-	100	nA

● ON CHARACTERISTICS

DC Current Gain (V_{CE} = 10V,I_C = 1mA) (V_{CE} = 10V,I_C = 10mA) (V_{CE} = 10V,I_C = 30mA)	 h_{FE1} h_{FE2} h_{FE3}	 25 40 40	 - - -	 - - -	 - - -
Collector-Emitter Saturation Voltages (I_C = 20mA, I_B = 2mA)	$V_{CE(sat)}$	-	-	500	mV
Base-Emitter Saturation Voltages (I_C = 20mA, I_B = 2mA)	$V_{BE(sat)}$	-	-	900	mV

● DYNAMIC CHARACTERISTICS

Current-Gain—Bandwidth Product (V_{CE} = 20V, I_C = 10mA, f = 100MHz)	f_T	50	-	-	MHz
Output Capacitance (V_{CB} = 20 Vdc, f = 1MHz)	C_{ob}	-	-	3	pF

Typical Characteristics

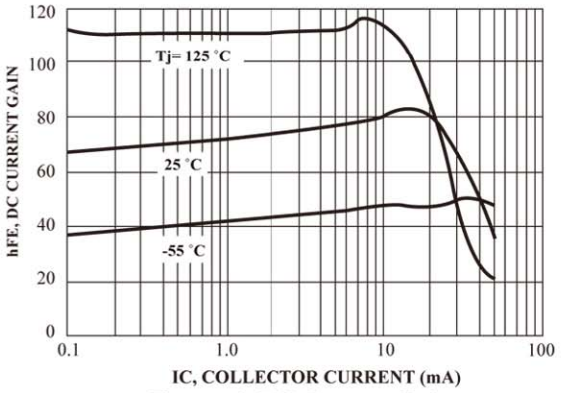


Figure .1 DC Current Gain

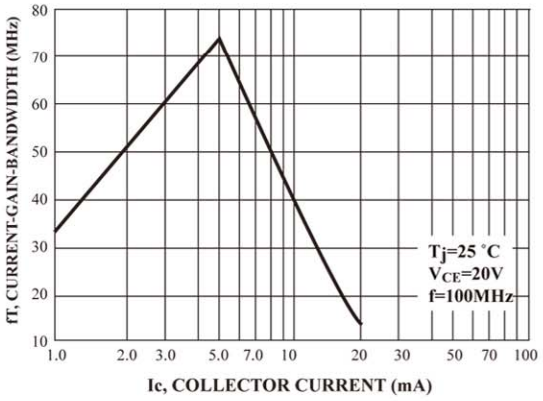


Figure .2 Current-Gain-Bandwidth

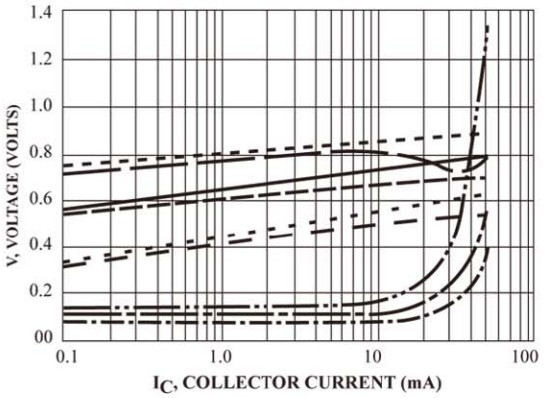
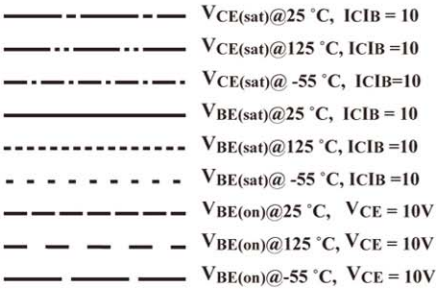
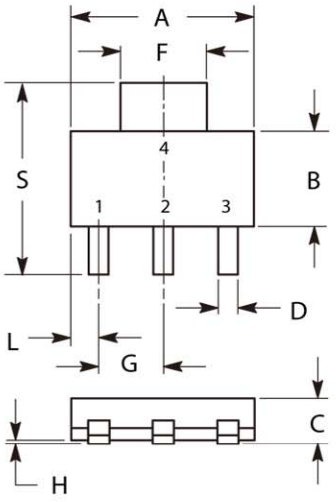


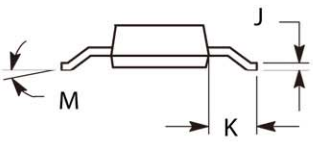
Figure.3 "On"Voltages



SOT-223 Outline Dimensions

unit:mm





DIM	MILLIMETERS MIN	MAX
A	6.30	6.70
B	3.30	3.70
C	1.50	1.75
D	0.60	0.89
F	2.90	3.20
G	2.20	2.40
H	0.020	0.100
J	0.24	0.35
K	1.50	2.00
L	0.85	1.05
M	0°	10°
S	6.70	7.30

单击下面可查看定价，库存，交付和生命周期等信息

>>SHIKUES(时科)